优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- BV_{CEO} > 20V
- I_C = 1A High Continuous Current
- Low Saturation Voltage $V_{CE(sat)}$ < 500mV @ 1A
- Complementary PNP Type: NK-BCX6925

Mechanical Data

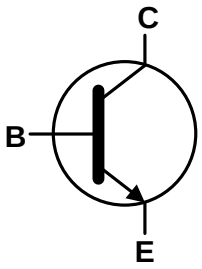
- Case: SOT89
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.055 grams (Approximate)

Application

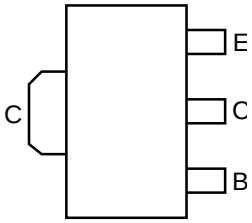
- Power MOSFET Gate Driving
- Low-Loss Power Switching

SOT89

Top View



Device Symbol



Top View
Pin Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	1	A
Peak Pulse Current	I_{CM}	2	A
Base Current	I_B	100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

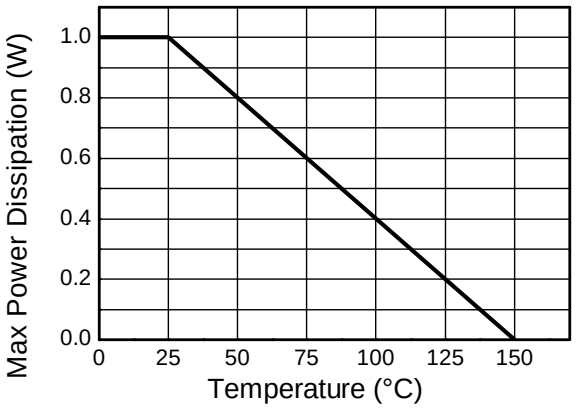
Characteristic	Symbol	Value	Unit
Collector Power Dissipation	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Leads (Note 6)	$R_{\theta JL}$	10.01	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

ESD Ratings (Note 7)

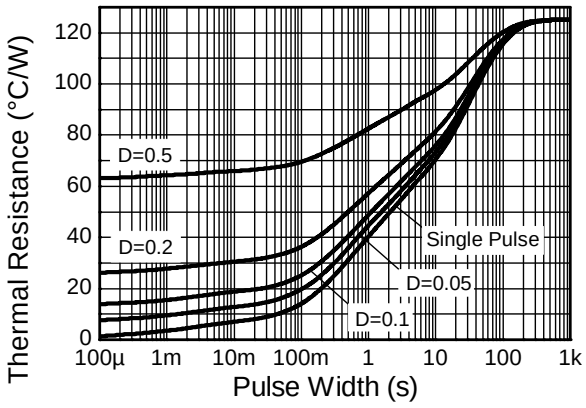
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

Notes:
5. For a device surface mounted on 15mm X 15mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; device measured when operating in steady state condition.
6. Thermal resistance from junction to solder-point (on the exposed collector pad).
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

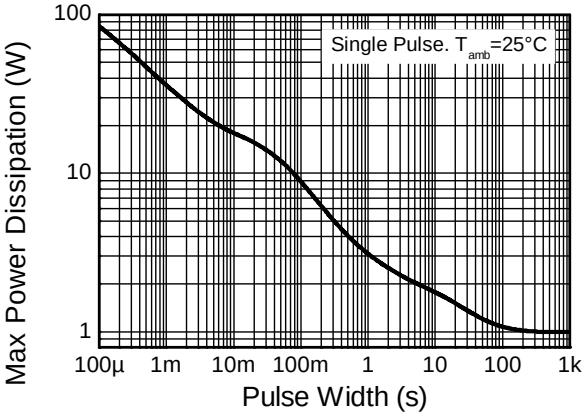
Thermal Characteristics and Derating Information



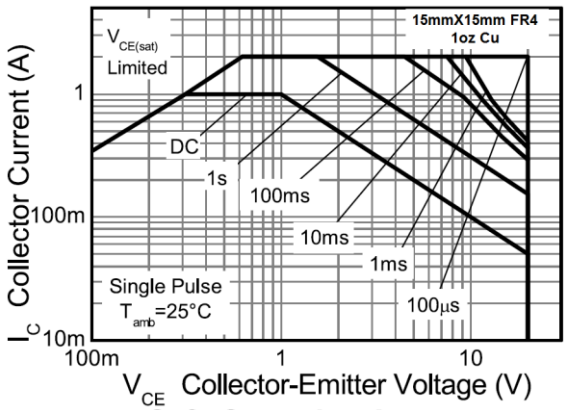
Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation



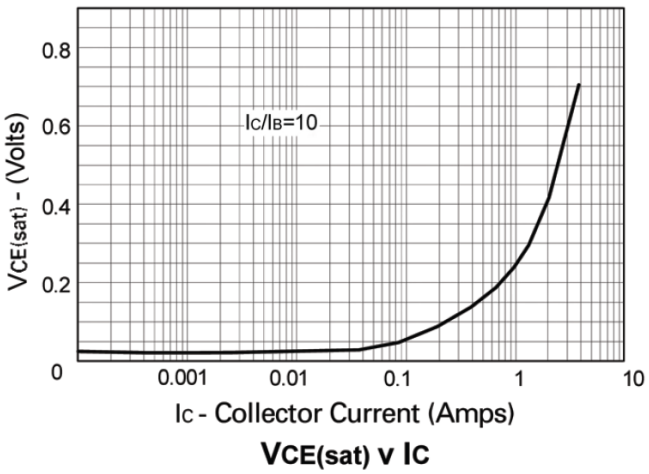
Safe Operating Area

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

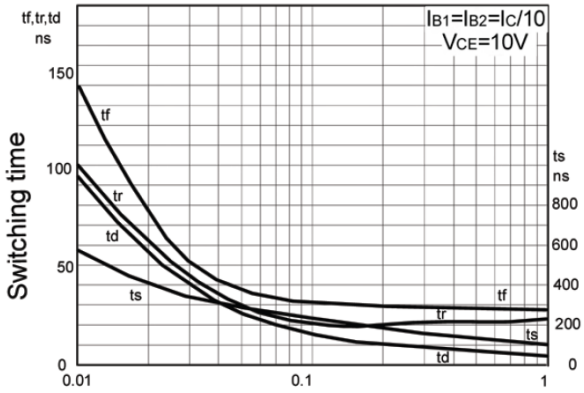
Characteristic	Symbol	Min	Typ.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	25	—	—	V	I_C = 100μA
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	20	—	—	V	I_C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	I_E = 100μA
Collector Cut-Off Current	I_{CBO}	—	—	100 10	nA μA	V_{CB} = 25V V_{CB} = 25V, T_A = +125°C
Emitter Cut-Off Current	I_{EBO}	—	—	100	nA	V_{EB} = 5V
DC Current Transfer Static Ratio (Note 8)	h_{FE}	50 160 60	— 250 —	— 400 —	—	I_C = 5mA, V_{CE} = 10V I_C = 500mA, V_{CE} = 1V I_C = 1A, V_{CE} = 1V
Collector-Emitter Saturation Voltage (Note 8)	$V_{CE(sat)}$	—	—	0.5	V	I_C = 1A, I_B = 100mA
Base-Emitter Turn-On Voltage (Note 8)	$V_{BE(on)}$	—	—	1.0	V	I_C = 1A, V_{CE} = 1V
Transitional Frequency	f_T	100	—	—	MHz	I_C = 100mA, V_{CE} = 5V, f = 100MHz
Output Capacitance	C_{obo}	—	—	25	pF	V_{CB} = 10V, f = 1MHz

Note: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

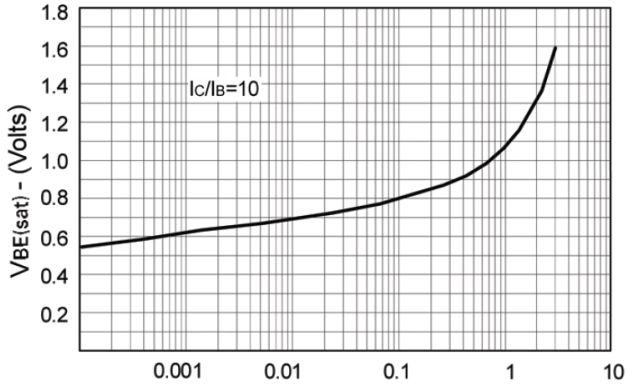
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



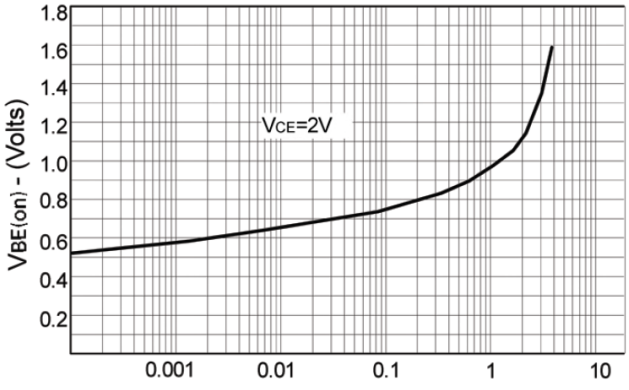
VCE(sat) v IC



Switching Speeds



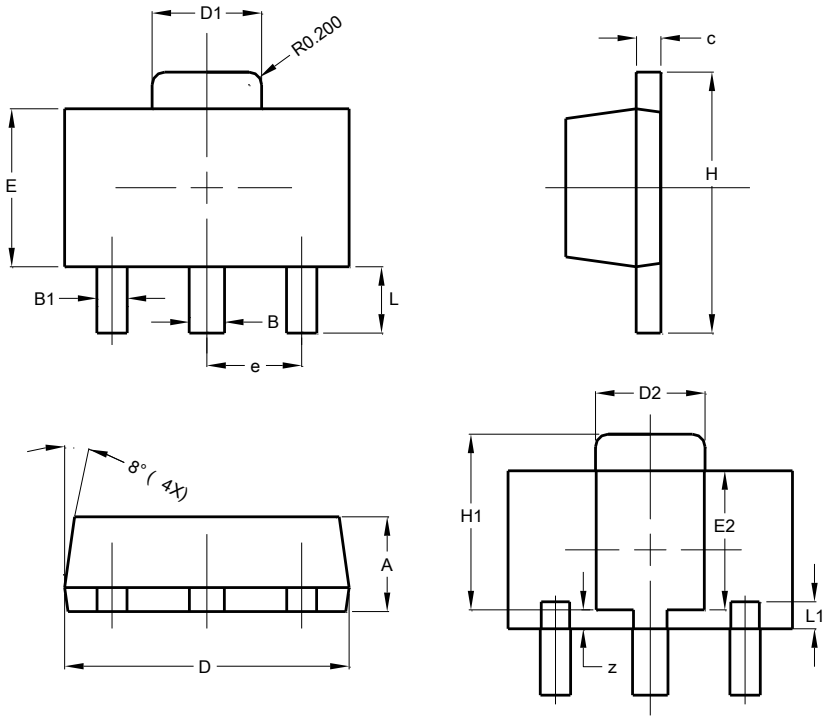
VBE(sat) v IC



VBE(on) v IC

Package Outline Dimensions

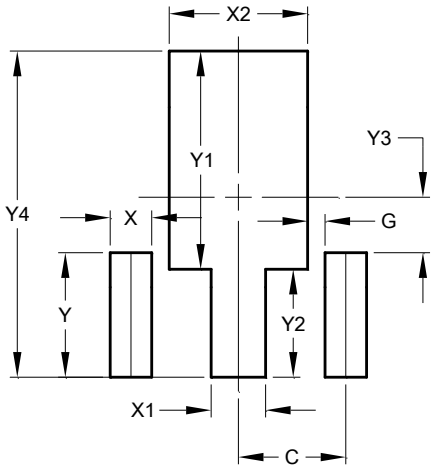
SOT89



SOT89			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530